IXTH60N20L2-VB Datasheet
N-Channel 200 V (D-S) 175 °C MOSFET

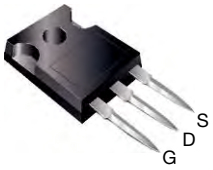
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A)	Q_g (TYP.)
200	0.021 at V_{GS} = 10 V	96	64 nC
	0.025 at V_{GS} = 7.5 V	90	

FEATURES

- Thunder power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested

RoHS COMPLIANT
HALOGEN FREE

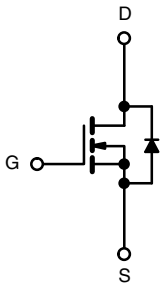
TO-247AC



Top View

APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	96	A
	T_C = 70 °C		75	
Pulsed Drain Current (t = 100 µs)		I_{DM}	240	
Avalanche Current	L = 0.1 mH	I_{AS}	60	
Single Avalanche Energy [a]		E_{AS}	180	mJ
Maximum Power Dissipation [a]	T_C = 25 °C	P_D	375 [b]	W
	T_C = 125 °C		125 [b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) [c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

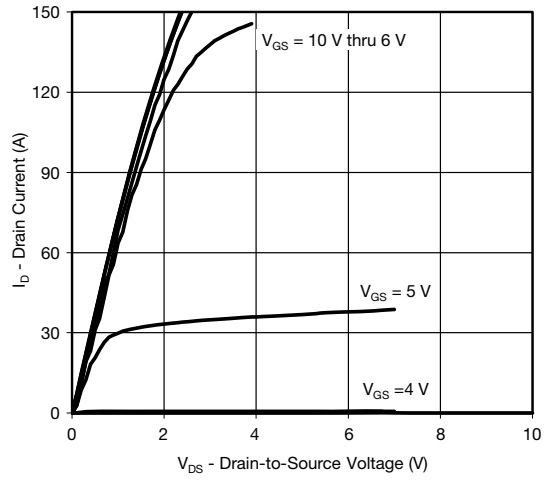
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	200	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3	-	5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 125 °C	-	-	150	
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 175 °C	-	-	5	mA
On-State Drain Current [a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	90	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A	–	0.021	-	Ω
		V_{GS} = 7.5 V, I_D = 30 A	--	0.025	-	
Forward Transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	-	75	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	4132	-	pF
Output Capacitance	C_{oss}		-	246	-	
Reverse Transfer Capacitance	C_{rss}		-	21	-	
Total Gate Charge [c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 60 A	-	64	96	nC
Gate-Source Charge [c]	Q_{gs}		-	16.7	-	
Gate-Drain Charge [c]	Q_{gd}		-	16.9	-	
Gate Resistance	R_g	f = 1 MHz	1.5	3	5	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 1.66 Ω I_D ≅ 60 A, V_{GEN} = 10 V, R_g = 1 Ω	-	13	26	ns
Rise Time [c]	t_r		-	112	200	
Turn-Off Delay Time [c]	$t_{d(off)}$		-	35	70	
Fall Time [c]	t_f		-	80	150	
Drain-Source Body Diode Ratings and Characteristics [b] (T_C = 25 °C)						
Pulsed Current (t = 100 µs)	I_{SM}		-	-	240	A
Forward Voltage [a]	V_{SD}	I_F = 10 A, V_{GS} = 0 V	-	0.8	1.2	V
Reverse Recovery Time	t_{rr}	I_F = 30 A, di/dt = 100 A/µs	-	160	320	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$		-	11	20	A
Reverse Recovery Charge	Q_{rr}		-	0.9	1.8	µC

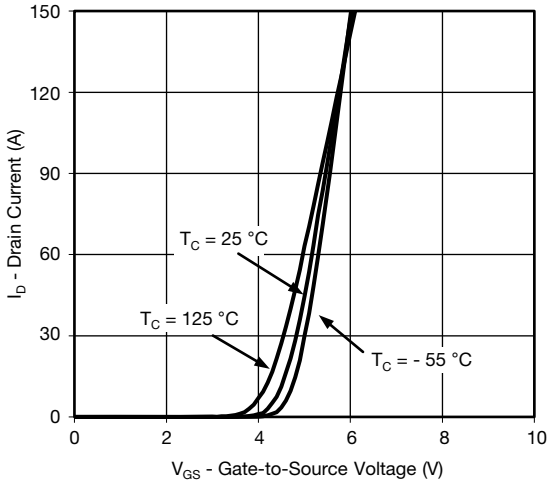
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

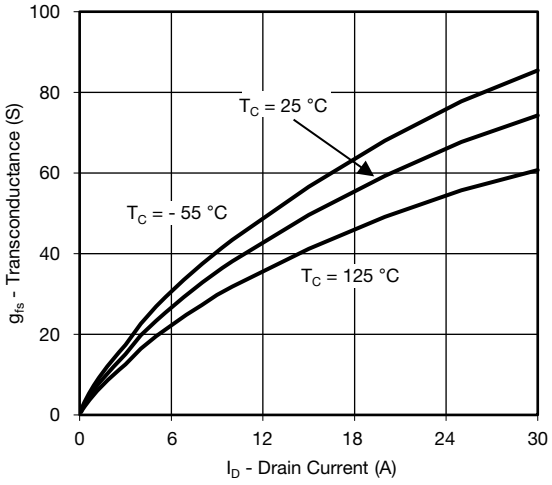
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



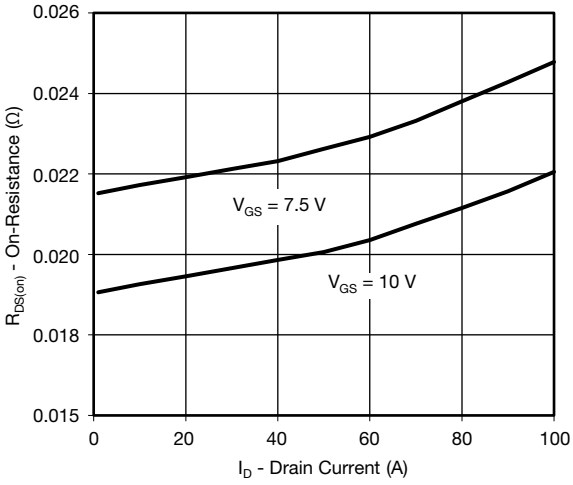
Output Characteristics



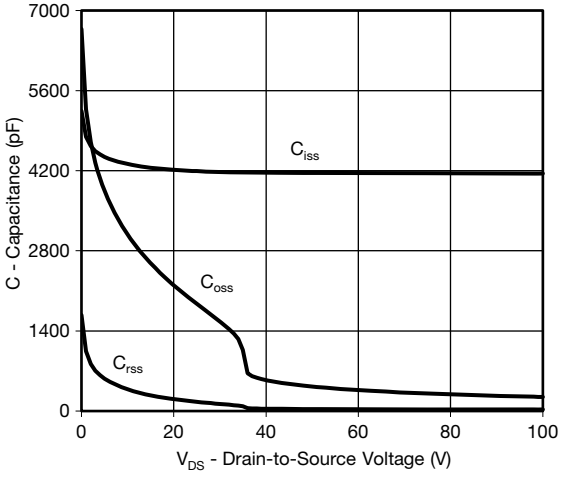
Transfer Characteristics



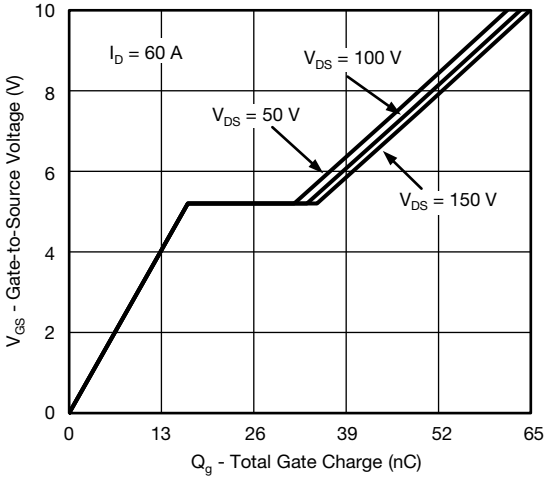
Transconductance



On-Resistance vs. Drain Current

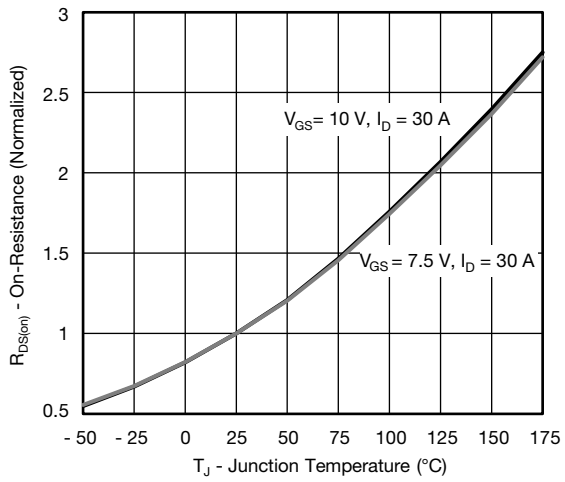


Capacitance

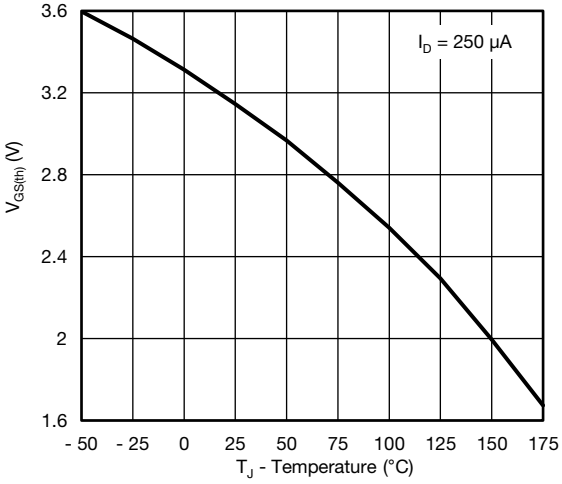


Gate Charge

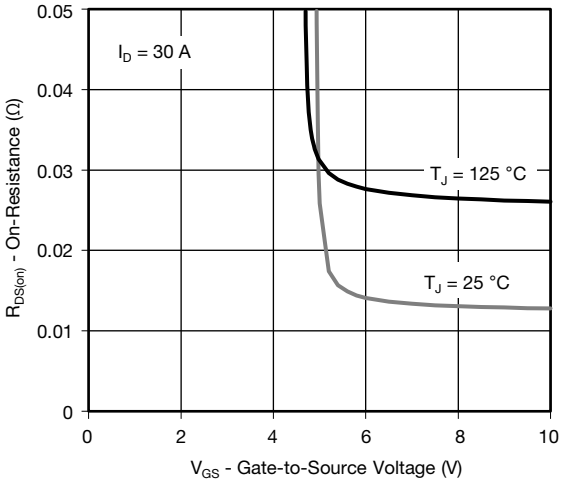
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



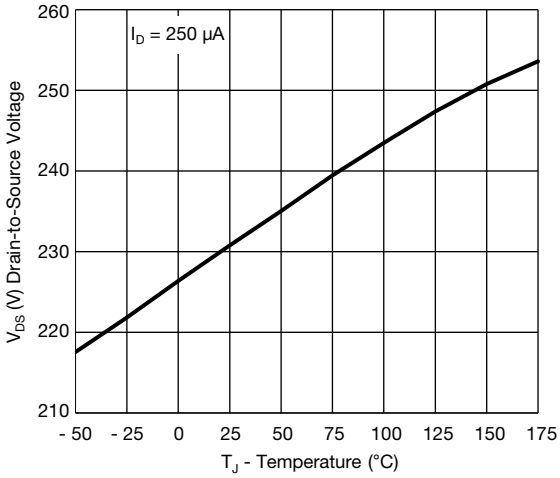
On-Resistance vs. Junction Temperature



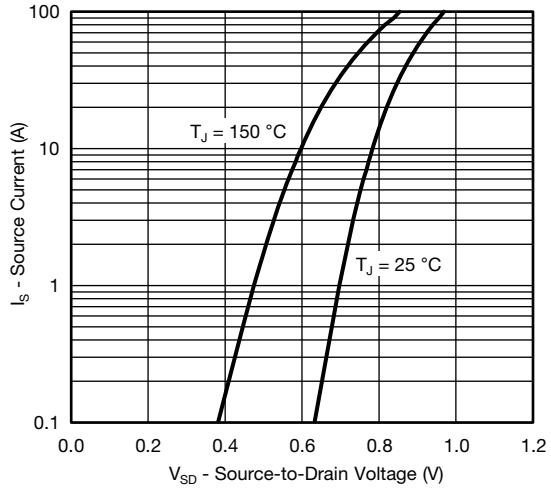
Threshold Voltage



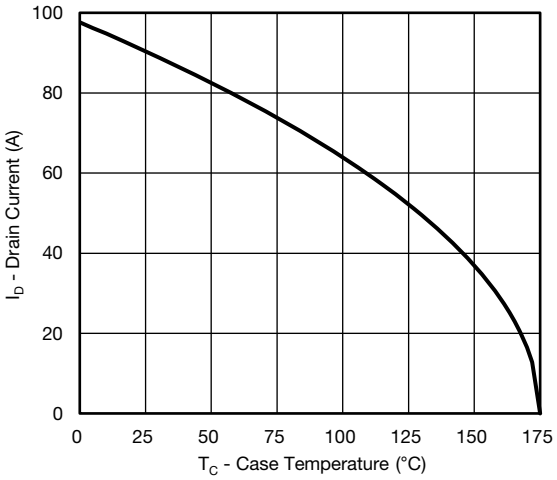
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

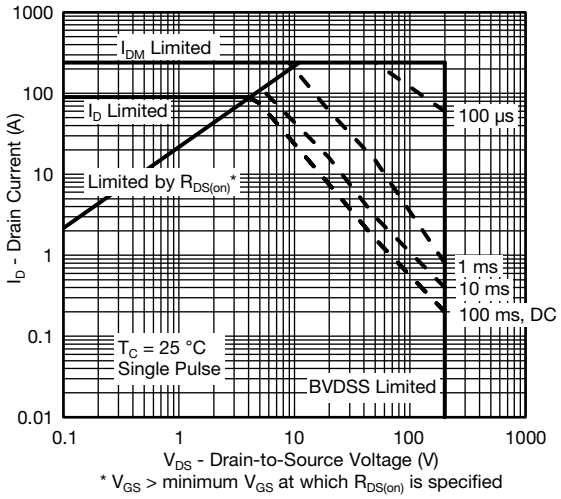


Source Drain Diode Forward Voltage

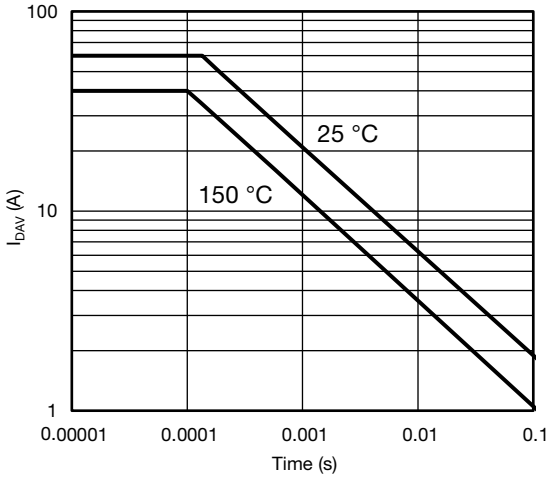


Current De-rating

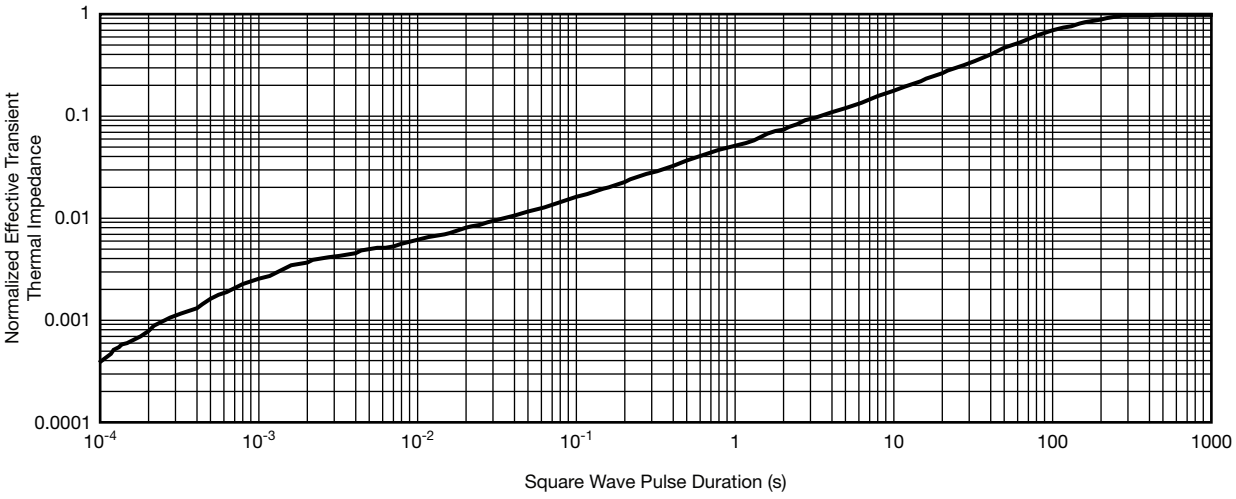
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

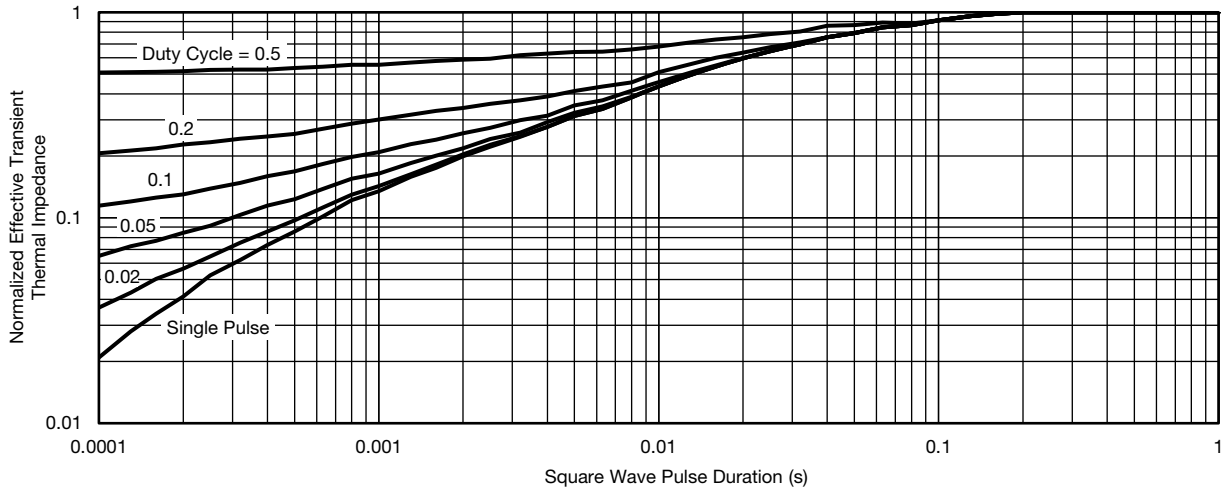


Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



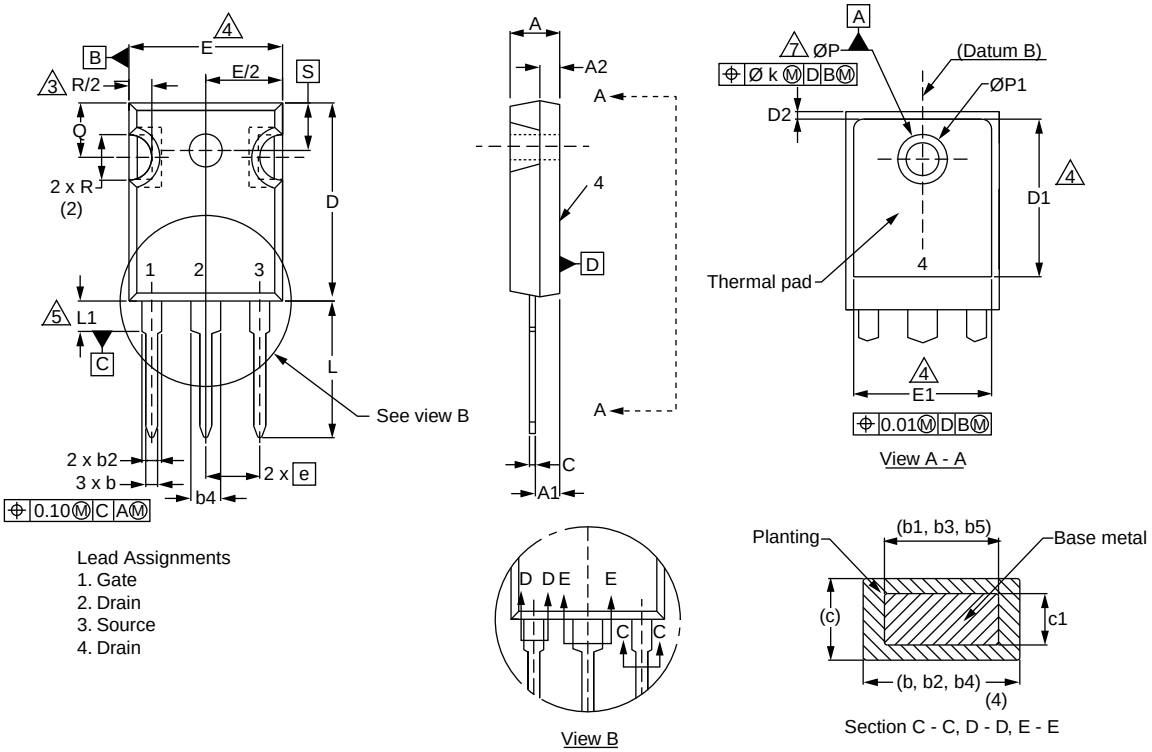
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-247AC (High Voltage)



Lead Assignments
1. Gate
2. Drain
3. Source
4. Drain

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

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